

PHASE CONTROL THYRISTORS

Hockey Puk Version

Features

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-24 (K-PUK)
- High profile hockey-puk

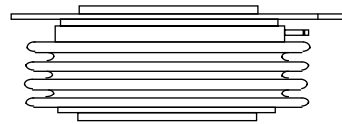
Typical Applications

- DC motor controls
- Controlled DC power supplies
- AC controllers

Major Ratings and Characteristics

Parameters	ST1280C..K	Units	
$I_{T(AV)}$	2310	A	
@ T_{hs}	55	°C	
$I_{T(RMS)}$	4150	A	
@ T_{hs}	25	°C	
I_{TSM}	@ 50Hz	42500	A
	@ 60Hz	44500	A
I^2t	@ 50Hz	9027	KA ² s
	@ 60Hz	8240	KA ² s
V_{DRM}/V_{RRM}	400 to 600	V	
t_q	typical	200	μs
T_J	- 40 to 125	°C	

2310A



case style A-24 (K-PUK)

ST1280C..K Series

Bulletin I25195 rev. B 02/00

International
 Rectifier

ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM} , max. repetitive peak and off-state voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_J$ max mA
ST1280C..K	04	400	500	100
	06	600	700	

On-state Conduction

Parameter	ST1280C..K	Units	Conditions	
$I_{T(AV)}$ Max. average on-state current @ Heatsink temperature	2310 (885)	A	180° conduction, half sine wave double side (single side) cooled	
	55 (85)	°C		
$I_{T(RMS)}$ Max. RMS on-state current	4150	A	@ 25°C heatsink temperature double side cooled	
I_{TSM} Max. peak, one-cycle non-repetitive surge current	42500		t = 10ms	No voltage
	44500		t = 8.3ms	reapplied
	35700		t = 10ms	100% V_{RRM}
	37400	t = 8.3ms	reapplied	
I^2t Maximum I^2t for fusing	9027	KA ² s	t = 10ms	No voltage
	8241		t = 8.3ms	reapplied
	6383		t = 10ms	100% V_{RRM}
	5828		t = 8.3ms	reapplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	90270	KA ² √s	t = 0.1 to 10ms, no voltage reapplied	
$V_{T(TO)1}$ Low level value of threshold voltage	0.83	V	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ max.	
$V_{T(TO)2}$ High level value of threshold voltage	0.90		$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ max.	
r_{t1} Low level value of on-state slope resistance	0.077	mΩ	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ max.	
r_{t2} High level value of on-state slope resistance	0.068		$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ max.	
V_{TM} Max. on-state voltage	1.44	V	$I_{pk} = 8000A$, $T_J = T_J$ max, $t_p = 10ms$ sine pulse	
I_H Maximum holding current	600	mA	$T_J = 25^\circ C$, anode supply 12V resistive load	
I_L Typical latching current	1000			

Switching

Parameter	ST1280C..K	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	1000	A/μs	Gate drive 20V, 20Ω, $t_r \leq 1\mu s$ $T_J = T_J$ max, anode voltage $\leq 80\% V_{DRM}$
t_d Typical delay time	1.9	μs	Gate current 1A, $di_g/dt = 1A/\mu s$ $V_d = 0.67\% V_{DRM}$, $T_J = 25^\circ C$
t_q Typical turn-off time	200		$I_{TM} = 550A$, $T_J = T_J$ max, $di/dt = 40A/\mu s$, $V_R = 50V$ $dv/dt = 20V/\mu s$, Gate 0V 100Ω, $t_p = 500\mu s$

Blocking

Parameter	ST1280C..K	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/ μ s	$T_J = T_J$ max. linear to 80% rated V_{DRM}
I_{RRM} I_{DRM} Max. peak reverse and off-state leakage current	100	mA	$T_J = T_J$ max, rated V_{DRM}/V_{RRM} applied

Triggering

Parameter	ST1280C..K	Units	Conditions
P_{GM} Maximum peak gate power	16	W	$T_J = T_J$ max, $t_p \leq 5$ ms
$P_{G(AV)}$ Maximum average gate power	3		$T_J = T_J$ max, $f = 50$ Hz, $d\% = 50$
I_{GM} Max. peak positive gate current	3.0	A	$T_J = T_J$ max, $t_p \leq 5$ ms
$+V_{GM}$ Maximum peak positive gate voltage	20	V	$T_J = T_J$ max, $t_p \leq 5$ ms
$-V_{GM}$ Maximum peak negative gate voltage	5.0		
I_{GT} DC gate current required to trigger	TYP.	MAX.	$T_J = -40^\circ\text{C}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$
	200	-	
	100	200	
V_{GT} DC gate voltage required to trigger	1.4	-	$T_J = -40^\circ\text{C}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$
	1.1	3.0	
	0.9	-	
I_{GD} DC gate current not to trigger	10	mA	$T_J = T_J$ max Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied
V_{GD} DC gate voltage not to trigger	0.25	V	

Thermal and Mechanical Specification

Parameter	ST1280C..K	Units	Conditions
T_J Max. operating temperature range	-40 to 125	$^\circ\text{C}$	
T_{stg} Max. storage temperature range	-40 to 150		
R_{thJ-hs} Max. thermal resistance, junction to heatsink	0.042 0.021	K/W	DC operation single side cooled DC operation double side cooled
R_{thC-hs} Max. thermal resistance, case to heatsink	0.006 0.003	K/W	DC operation single side cooled DC operation double side cooled
F Mounting force, $\pm 10\%$	24500 (2500)	N (Kg)	
wt Approximate weight	425	g	
Case style	A-24 (K-PUK)		See Outline Table

ST1280C..K Series

Bulletin I25195 rev. B 02/00

International
IRF Rectifier

ΔR_{thJ-hs} Conduction

(The following table shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	Single Side	Double Side	Single Side	Double Side		
180°	0.003	0.003	0.002	0.002	K/W	$T_J = T_{J \text{ max.}}$
120°	0.004	0.004	0.004	0.004		
90°	0.005	0.005	0.005	0.005		
60°	0.007	0.007	0.007	0.007		
30°	0.012	0.012	0.012	0.012		

Ordering Information Table

Device Code							
ST	128	0	C	06	K	1	
①	②	③	④	⑤	⑥	⑦	⑧
1	- Thyristor	2	- Essential part number	3	- 0 = Converter grade	4	- C = Ceramic Puk
5	- Voltage code: Code x 100 = V_{RRM} (See Voltage Rating Table)	6	- K = Puk Case A-24(K-PUK)	7	- 0 = Eyelet terminals (Gate and Auxiliary Cathode Unsoldered Leads)	1 = Fast-on terminals (Gate and Auxiliary Cathode Unsoldered Leads)	2 = Eyelet terminals (Gate and Auxiliary Cathode Soldered Leads)
7	- 1 = Fast-on terminals (Gate and Auxiliary Cathode Soldered Leads)	3	- Fast-on terminals (Gate and Auxiliary Cathode Soldered Leads)	8	- Critical dv/dt: None = 500V/ μ sec (Standard selection)	L = 1000V/ μ sec (Special selection)	

Outline Table

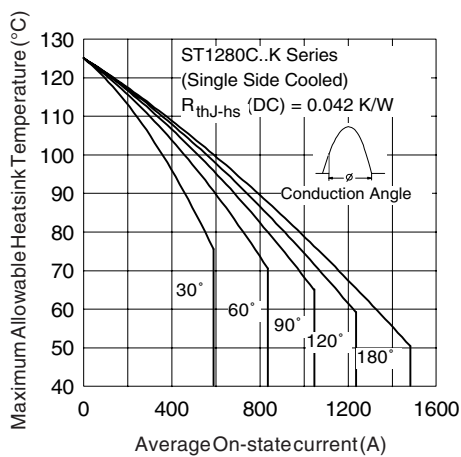
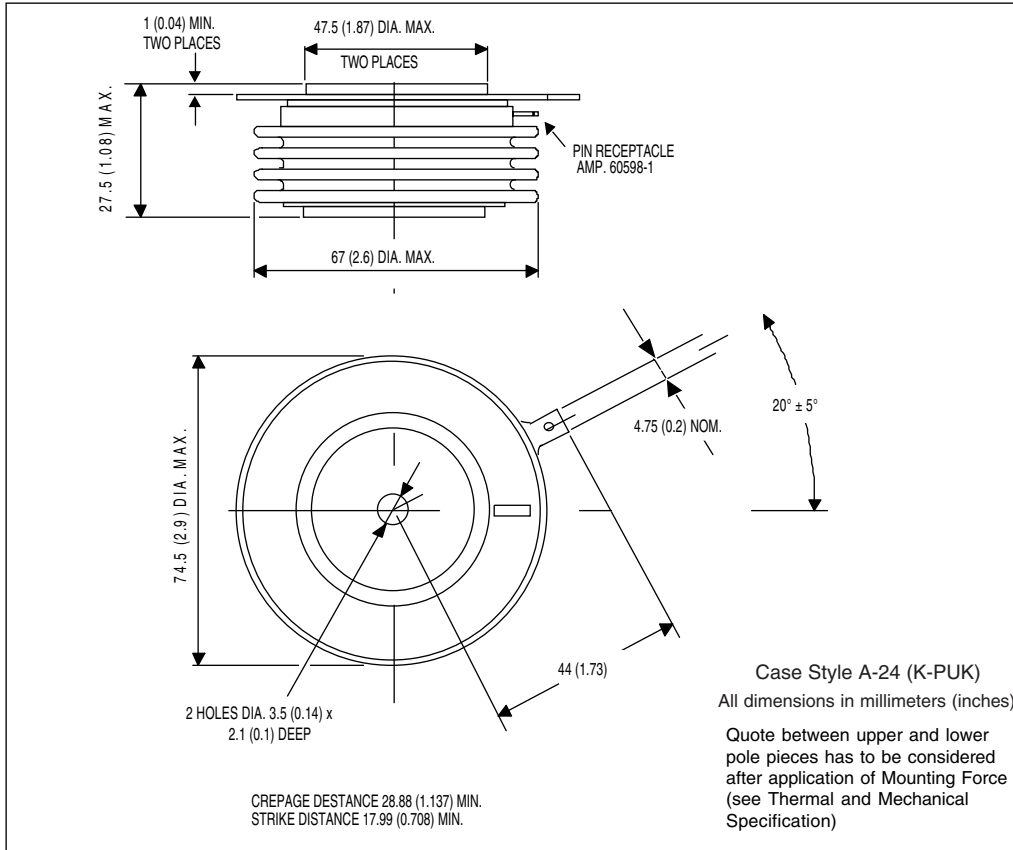


Fig. 1 - Current Ratings Characteristics

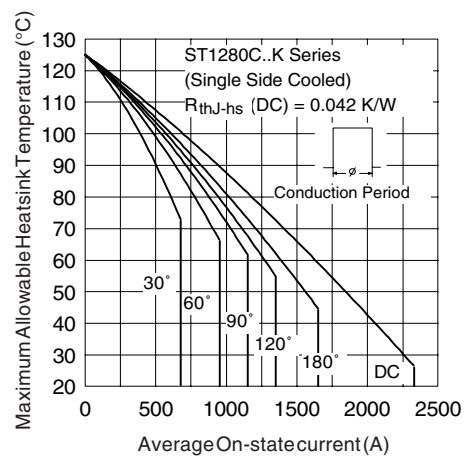


Fig. 2 - Current Ratings Characteristics

ST1280C..K Series

Bulletin I25195 rev. B 02/00

International
IRF Rectifier

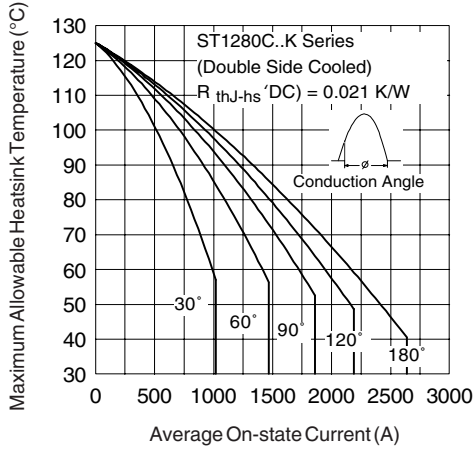


Fig. 3 - Current Ratings Characteristics

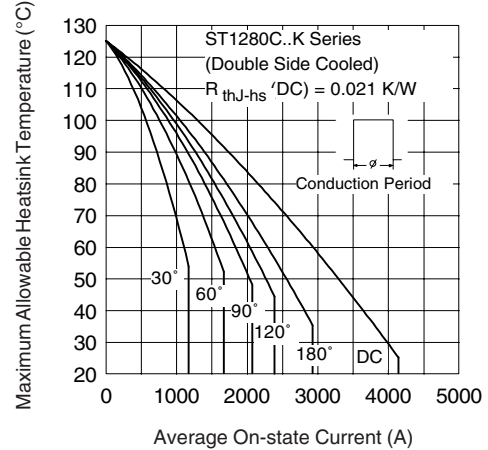


Fig. 4 - Current Ratings Characteristics

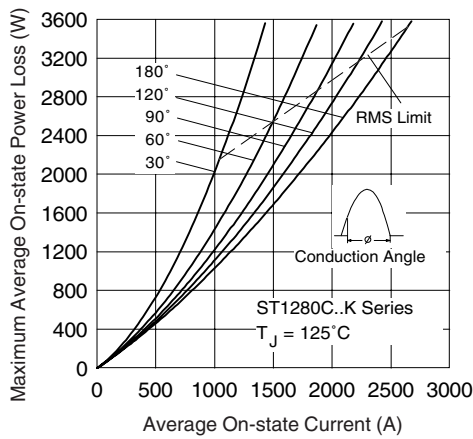


Fig. 5 - On-state Power Loss Characteristics

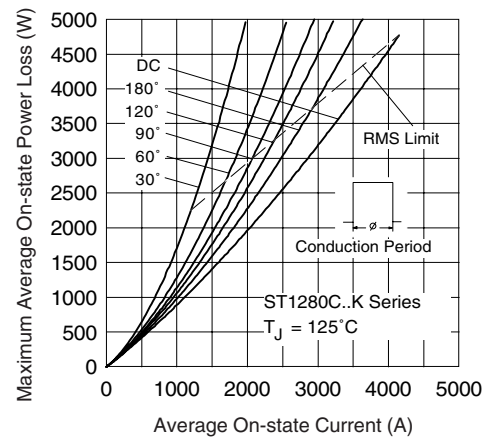


Fig. 6 - On-state Power Loss Characteristics

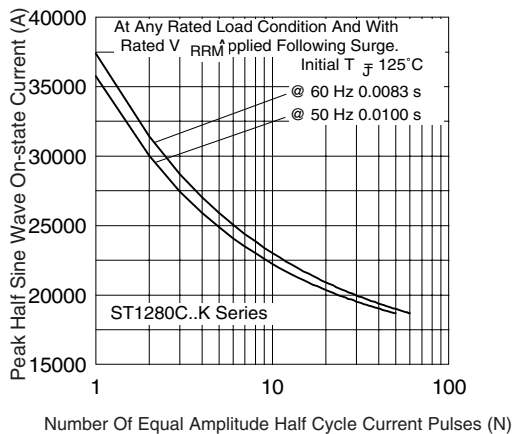


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

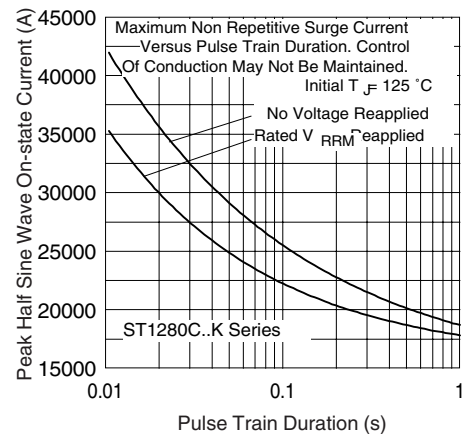


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

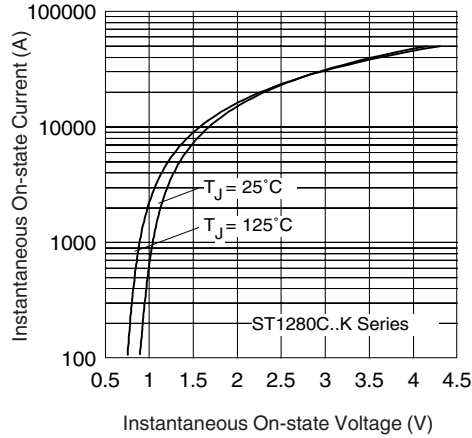


Fig. 9 - On-state Voltage Drop Characteristics

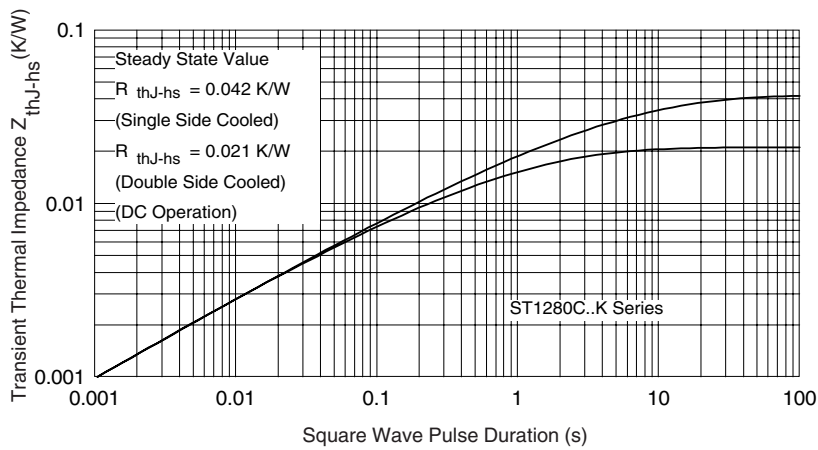


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

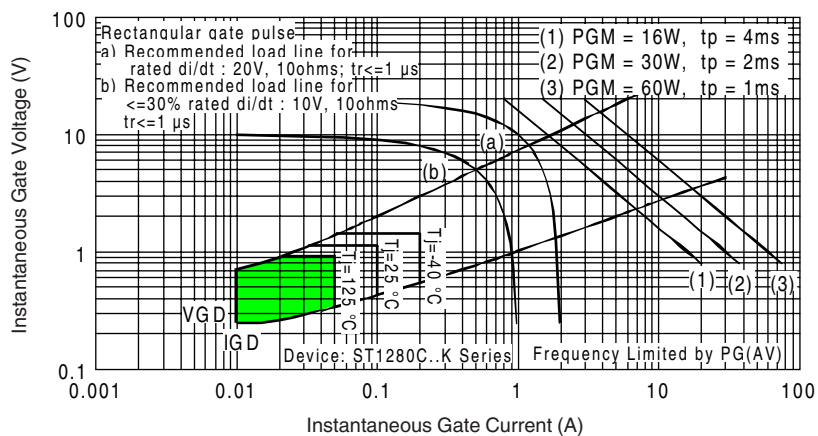


Fig. 11 - Gate Characteristics